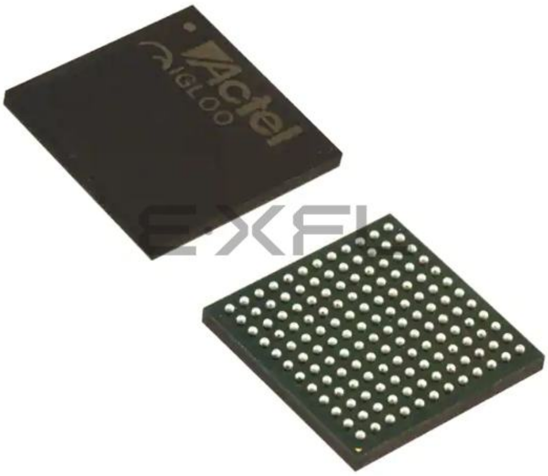
Microchip Technology - M1A3P600L-1FGG144 Datasheet



Welcome to **E-XFL.COM**

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p600l-1fgg144

Email: info@E-XFL.COM
Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Set/Reset

Since all I/Os and globals are tied High in Flash*Freeze mode (unless hold state is used on IGLOO nano or IGLOO PLUS), Microsemi recommends using active low set/reset at the top-level port. If needed, the signal can be inverted internally.

- If the intention is to always set/reset in Flash*Freeze mode, a self set/reset circuit may be implemented to accomplish this, as shown in Figure 2-9. Configure an active High set/reset input pin so it uses the internal pull-up during Flash*Freeze mode, and drives Low during active mode. When the device exits Flash*Freeze mode, the input will transition from High to Low, releasing the set/reset. Note that this circuit may release set/reset before all outputs become active, since outputs are enabled up to 200 ns after inputs when exiting Flash*Freeze mode.

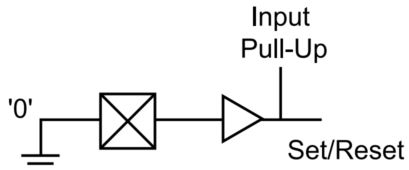


Figure 2-9 • **Flash*Freeze Self-Reset Circuit**

I/Os

- Floating inputs can cause totem pole currents on the input I/O circuitry when the device is in active mode. If inputs will be released (undriven) during Flash*Freeze mode, Microsemi recommends that they are only released after the device enters Flash*Freeze mode.
- As mentioned earlier, asynchronous input to output paths are subject to possible glitching when entering Flash*Freeze mode. For example, on a direct in-to-out path, if the current state is '0' and the input bank deactivates first, the input and then the output will transition to '1' before the output enters its Flash*Freeze state. This can be prevented by using latches along with Flash*Freeze management IP to gate asynchronous in-to-out paths prior to entering Flash*Freeze mode.

JTAG

- The JTAG state machine is powered but not active during Flash*Freeze mode.
- TCK should be held in a static state to prevent dynamic power consumption of the JTAG circuit during Flash*Freeze.
- Specific JTAG pin tie-off recommendations suitable for Flash*Freeze mode can be found in the "Pin Descriptions and Packaging" chapter of the device datasheet.

ULSICC

- The User Low Static ICC (ULSICC) macro acts as an access point to the hard Flash*Freeze technology block in the device. The ULSICC macro represents a hard, fixed location block in the device. When the LSICC input of the ULSICC macro is driven Low, the Flash*Freeze pin is blocked, and when LSICC is driven High, the Flash*Freeze pin is enabled.
- If the user decides to build his/her own Flash*Freeze type 2 clock and data management logic, note that the LSICC signal on the ULSICC macro is ANDed internally with the Flash*Freeze signal. In order to reliably enter Flash*Freeze, the LSICC signal must remain asserted High while entering and during Flash*Freeze mode.

*Flash*Freeze Management IP*

One of the key benefits of Microsemi's Flash*Freeze mode is the ability to preserve the state of all internal registers, SRAM content, and I/Os (IGLOO nano and IGLOO PLUS only). This feature enables seamless continuation of data processing before and after Flash*Freeze, without the need to reload or reinitialize the FPGA system. Microsemi's Flash*Freeze management IP, available for type 2 implementation, offers a robust RTL block that ensures clean clock gating of all system clocks before entering and upon exiting Flash*Freeze mode. This IP also gives users the option to perform housekeeping prior to entering Flash*Freeze mode. This section will provide an overview of the

CCC Support in Microsemi's Flash Devices

The flash FPGAs listed in Table 4-1 support the CCC feature and the functions described in this document.

***Table 4-1* • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: **The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 4-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 4-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

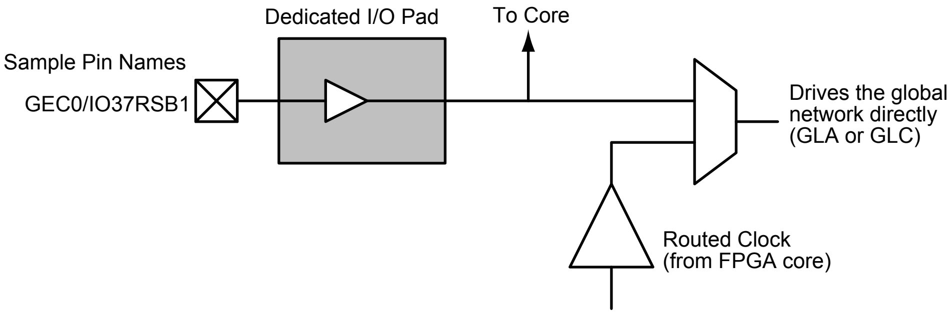
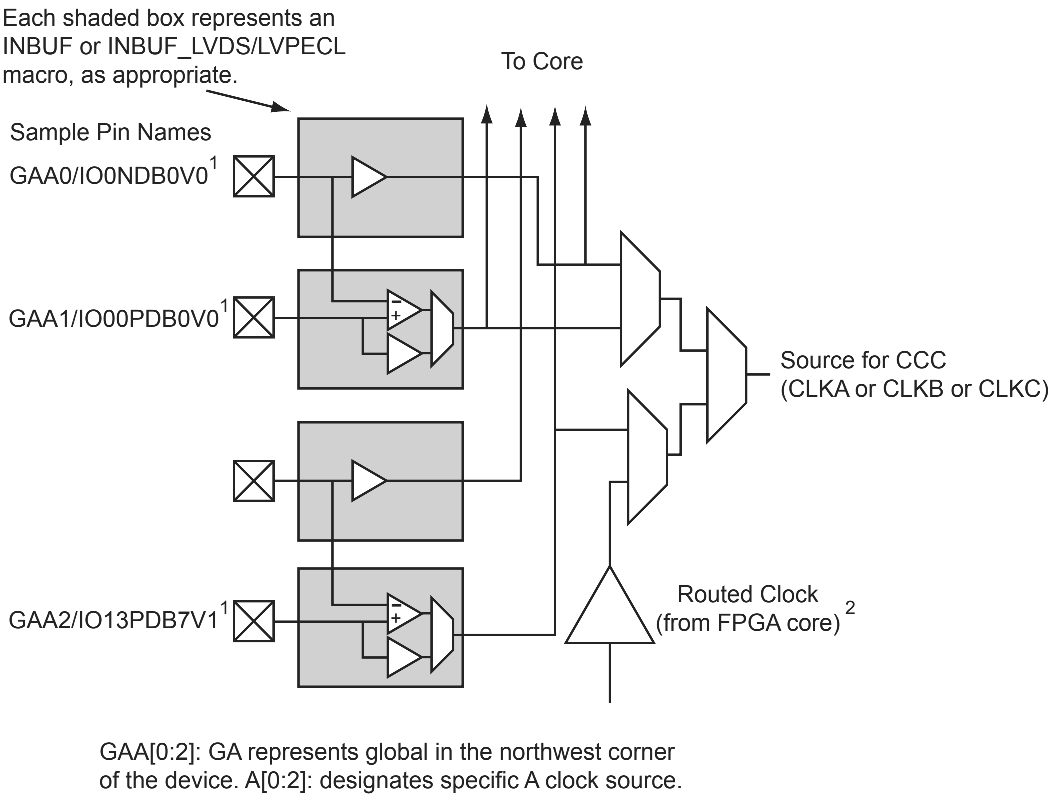


Figure 4-7 **• Clock Input Sources (30 k gates devices and below)**



Notes:

1. *Represents the global input pins. Globals have direct access to the clock conditioning block and are not routed via the FPGA fabric. Refer to the "User I/O Naming Conventions in I/O Structures" chapter of the appropriate device user's guide.*
2. *Instantiate the routed clock source input as follows:*
   - *a) Connect the output of a logic element to the clock input of a PLL, CLKDLY, or CLKINT macro.*
   - *b) Do not place a clock source I/O (INBUF or INBUF_LVPECL/LVDS/B-LVDS/M-LVDS/DDR) in a relevant global pin location.*
3. *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

Figure 4-8 **• Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT (60 k gates devices and above)**

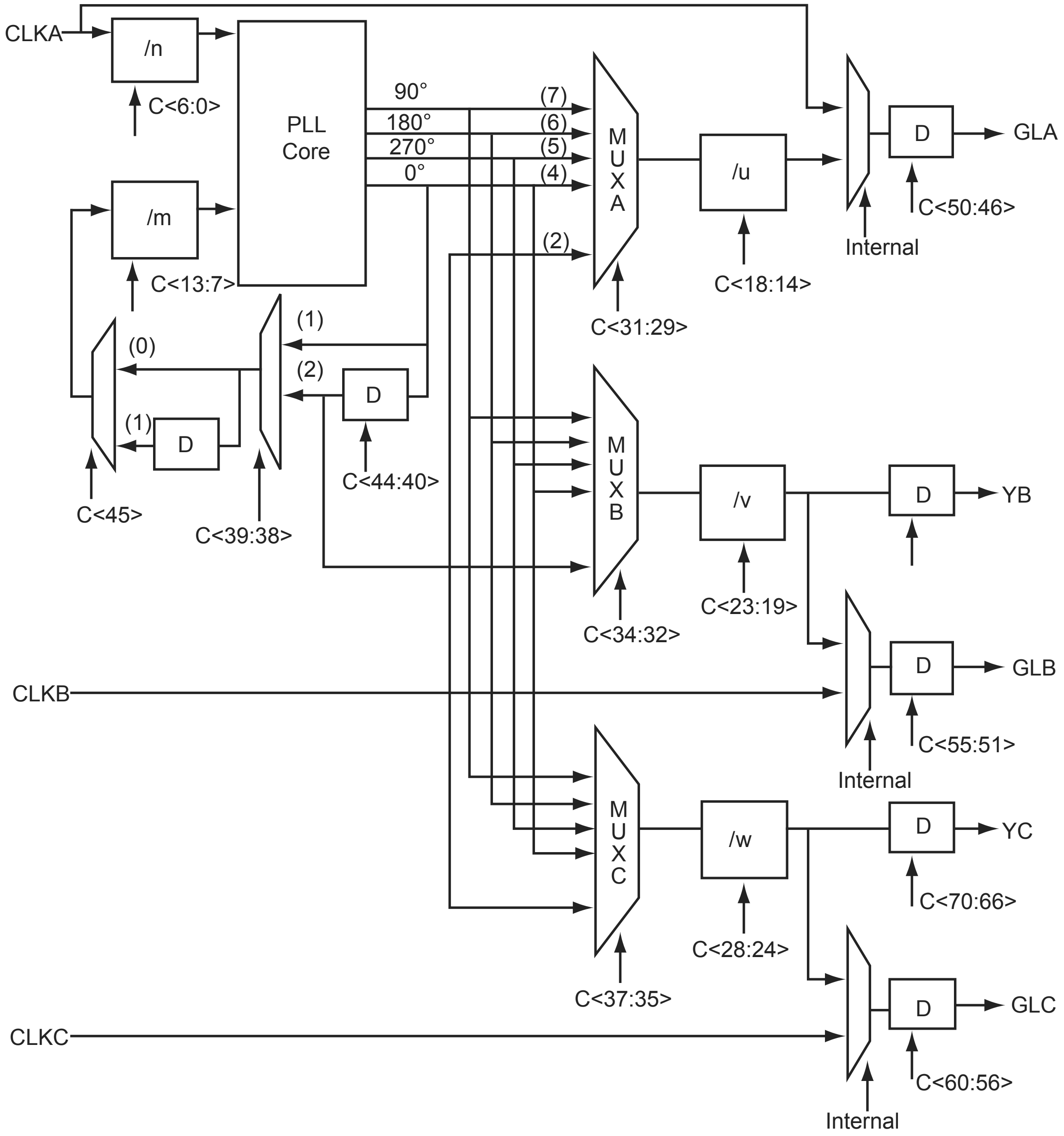


Figure 4-22 • **CCC Block Control Bits – Graphical Representation of Assignments**

```
  DYNCCC Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN), .GLA(GLA), .LOCK(LOCK),
    .CLKB(CLKB), .GLB(GLB), .YB(), .CLKC(CLKC), .GLC(GLC), .YC(), .SDIN(SDIN),
    .SCLK(SCLK), .SSHIFT(SSHIFT), .SUPDATE(SUPDATE), .MODE(MODE), .SDOUT(SDOUT),
    .OADIV0(GND), .OADIV1(GND), .OADIV2(VCC), .OADIV3(GND), .OADIV4(GND), .OAMUX0(GND),
    .OAMUX1(GND), .OAMUX2(VCC), .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND),
    .DLYGLA3(GND), .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND),
    .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND), .OBMUX2(GND), .DLYYB0(GND),
    .DLYYB1(GND), .DLYYB2(GND), .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND),
    .DLYGLB1(GND), .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND),
    .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND), .OCMUX0(GND), .OCMUX1(GND),
    .OCMUX2(GND), .DLYYC0(GND), .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND),
    .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND), .DLYGLC4(GND),
    .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(VCC), .FINDIV3(GND), .FINDIV4(GND),
    .FINDIV5(GND), .FINDIV6(GND), .FBDIV0(GND), .FBDIV1(GND), .FBDIV2(GND),
    .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(VCC), .FBDIV6(GND), .FBDLY0(GND), .FBDLY1(GND),
    .FBDLY2(GND), .FBDLY3(GND), .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND),
    .XDLYSEL(GND), .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(VCC));
  defparam Core.VCOFREQUENCY = 165.000;

endmodule
```

Delayed Clock Configuration

The CLKDLY macro can be generated with the desired delay and input clock source (Hardwired I/O, External I/O, or Core Logic), as in Figure 4-28.

Figure 4-28 **• Delayed Clock Configuration Dialog Box**

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
****************
Macro Parameters
****************

Name                            : delay_macro
Family                          : ProASIC3
Output Format                   : Verilog
Type                            : Delayed Clock
Delay Index                     : 2
CLKA Source                     : Hardwired I/O

Total Clock Delay = 0.935 ns.

The resultant CLKDLY macro Verilog netlist is as follows:

module delay_macro(GL,CLK);

output GL;
input  CLK;
```

Date	Changes	Page
v1.2 (June 2008)	The following changes were made to the family descriptions in Figure 4-1 • Overview of the CCCs Offered in Fusion, IGLOO, and ProASIC3: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	77
v1.1 (March 2008)	Table 4-1 • Flash-Based FPGAs and the associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	79
	The "Global Input Selections" section was updated to include 15 k gate devices as supported I/O types for globals, for CCC only.	87
	Table 4-5 • Number of CCCs by Device Size and Package was revised to include ProASIC3L, IGLOO PLUS, A3P015, AGL015, AGLP030, AGLP060, and AGLP125.	94
	The "IGLOO and ProASIC3 CCC Locations" section was revised to include 15 k gate devices in the exception statements, as they do not contain PLLs.	97
v1.0 (January 2008)	Information about unlocking the PLL was removed from the "Dynamic PLL Configuration" section.	103
	In the "Dynamic PLL Configuration" section, information was added about running Layout and determining the exact setting of the ports.	116
	In Table 4-8 • Configuration Bit Descriptions for the CCC Blocks, the following bits were updated to delete "transport to the user" and reference the footnote at the bottom of the table: 79 to 71.	106

Table 6-2 **• Allowable Aspect Ratio Settings for WIDTHA[1:0]**

WIDTHA[1:0]	WIDTHB[1:0]	D×W
00	00	4k×1
01	01	2k×2
10	10	1k×4
11	11	512×9

Note: The aspect ratio settings are constant and cannot be changed on the fly.

BLKA and BLKB

These signals are active-low and will enable the respective ports when asserted. When a BLKx signal is deasserted, that port's outputs hold the previous value.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, BLKB should be tied to ground.

WENA and WENB

These signals switch the RAM between read and write modes for the respective ports. A LOW on these signals indicates a write operation, and a HIGH indicates a read.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WENB should be tied to ground.

CLKA and CLKB

These are the clock signals for the synchronous read and write operations. These can be driven independently or with the same driver.

Note: For Automotive ProASIC3 devices, dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile.

PIPEA and PIPEB

These signals are used to specify pipelined read on the output. A LOW on PIPEA or PIPEB indicates a nonpipelined read, and the data appears on the corresponding output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the corresponding output in the next clock cycle.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, PIPEB should be tied to ground. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

WMODEA and WMODEB

These signals are used to configure the behavior of the output when the RAM is in write mode. A LOW on these signals makes the output retain data from the previous read. A HIGH indicates pass-through behavior, wherein the data being written will appear immediately on the output. This signal is overridden when the RAM is being read.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WMODEB should be tied to ground.

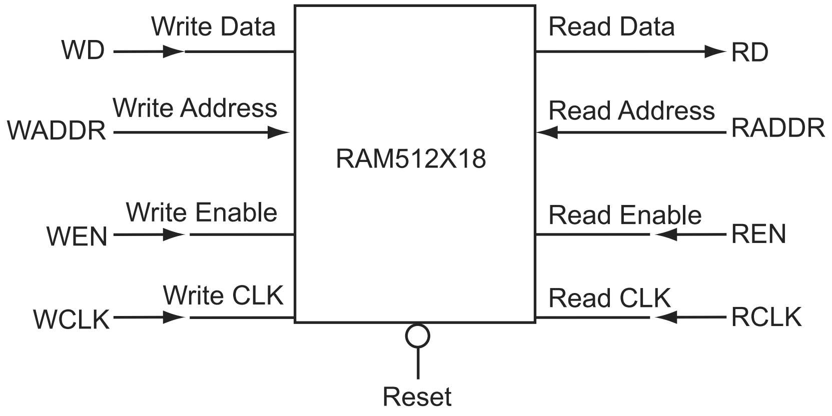
RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

ADDRA and ADDRB

These are used as read or write addresses, and they are 12 bits wide. When a depth of less than 4 k is specified, the unused high-order bits must be grounded (Table 6-3 on page 155).



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet.

Figure 6-5 **• 512X18 Two-Port RAM Block Diagram**

Signal Descriptions for RAM512X18

RAM512X18 has slightly different behavior from RAM4K9, as it has dedicated read and write ports.

WW and RW

These signals enable the RAM to be configured in one of the two allowable aspect ratios (Table 6-5).

Table 6-5 **• Aspect Ratio Settings for WW[1:0]**

WW[1:0]	RW[1:0]	D×W
01	01	512×9
10	10	256×18
00, 11	00, 11	Reserved

WD and RD

These are the input and output data signals, and they are 18 bits wide. When a 512×9 aspect ratio is used for write, WD[17:9] are unused and must be grounded. If this aspect ratio is used for read, RD[17:9] are undefined.

WADDR and RADDR

These are read and write addresses, and they are nine bits wide. When the 256×18 aspect ratio is used for write or read, WADDR[8] and RADDR[8] are unused and must be grounded.

WCLK and RCLK

These signals are the write and read clocks, respectively. They can be clocked on the rising or falling edge of WCLK and RCLK.

WEN and REN

These signals are the write and read enables, respectively. They are both active-low by default. These signals can be configured as active-high.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

PIPE

This signal is used to specify pipelined read on the output. A LOW on PIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

Example of RAM Initialization

This section of the document presents a sample design in which a 4×4 RAM block is being initialized through the JTAG port. A test feature has been implemented in the design to read back the contents of the RAM after initialization to verify the procedure.

The interface block of this example performs two major functions: initialization of the RAM block and running a test procedure to read back the contents. The clock output of the interface is either the write clock (for initialization) or the read clock (for reading back the contents). The Verilog code for the interface block is included in the "Sample Verilog Code" section on page 167.

For simulation purposes, users can declare the input ports of the UJTAG macro for easier assignment in the testbench. However, the UJTAG input ports should not be declared on the top level during synthesis. If the input ports of the UJTAG are declared during synthesis, the synthesis tool will instantiate input buffers on these ports. The input buffers on the ports will cause Compile to fail in Designer.

Figure 6-10 shows the simulation results for the initialization step of the example design.

The CLK_OUT signal, which is the clock output of the interface block, is the inverted DR_UPDATE output of the UJTAG macro. It is clear that it gives sufficient time (while the TAP Controller is in the Data Register Update state) for the write address and data to become stable before loading them into the RAM block.

Figure 6-11 presents the test procedure of the example. The data read back from the memory block matches the written data, thus verifying the design functionality.

***Figure 6-10* • Simulation of Initialization Step**

***Figure 6-11* • Simulation of the Test Procedure of the Example**

Features Supported on Every I/O

Table 7-5 lists all features supported by transmitter/receiver for single-ended and differential I/Os. Table 7-6 on page 180 lists the performance of each I/O technology.

Table 7-5 **• I/O Features**

Feature	Description
All I/O	• High performance (Table 7-6 on page 180) • Electrostatic discharge (ESD) protection • I/O register combining option
Single-Ended Transmitter Features	• Hot-swap: – 30K gate devices: hot-swap in every mode – All other IGLOO and ProASIC3 devices: no hot-swap • Output slew rate: 2 slew rates (except 30K gate devices) • Weak pull-up and pull-down resistors • Output drive: 3 drive strengths • Programmable output loading • Skew between output buffer enable/disable time: 2 ns delay on rising edge and 0 ns delay on falling edge (see the "Selectable Skew between Output Buffer Enable and Disable Times" section on page 199 for more information) • LVTTL/LVCMOS 3.3 V outputs compatible with 5 V TTL inputs
Single-Ended Receiver Features	• 5 V–input–tolerant receiver (Table 7-12 on page 193) • Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
Differential Receiver Features—250K through 1M Gate Devices	• Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
CMOS-Style LVDS, B-LVDS, M-LVDS, or LVPECL Transmitter	• Two I/Os and external resistors are used to provide a CMOS-style LVDS, DDR LVDS, B-LVDS, and M-LVDS/LVPECL transmitter solution. • High slew rate • Weak pull-up and pull-down resistors • Programmable output loading

I/O Architecture

I/O Tile

The I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired (Figure 7-2). The registers can also be used to support the JESD-79C Double Data Rate (DDR) standard within the I/O structure (see the "DDR for Microsemi's Low Power Flash Devices" section on page 271 for more information). In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired (Figure 7-2).

As depicted in Figure 7-2, all I/O registers share one CLR port. The output register and output enable register share one CLK port.

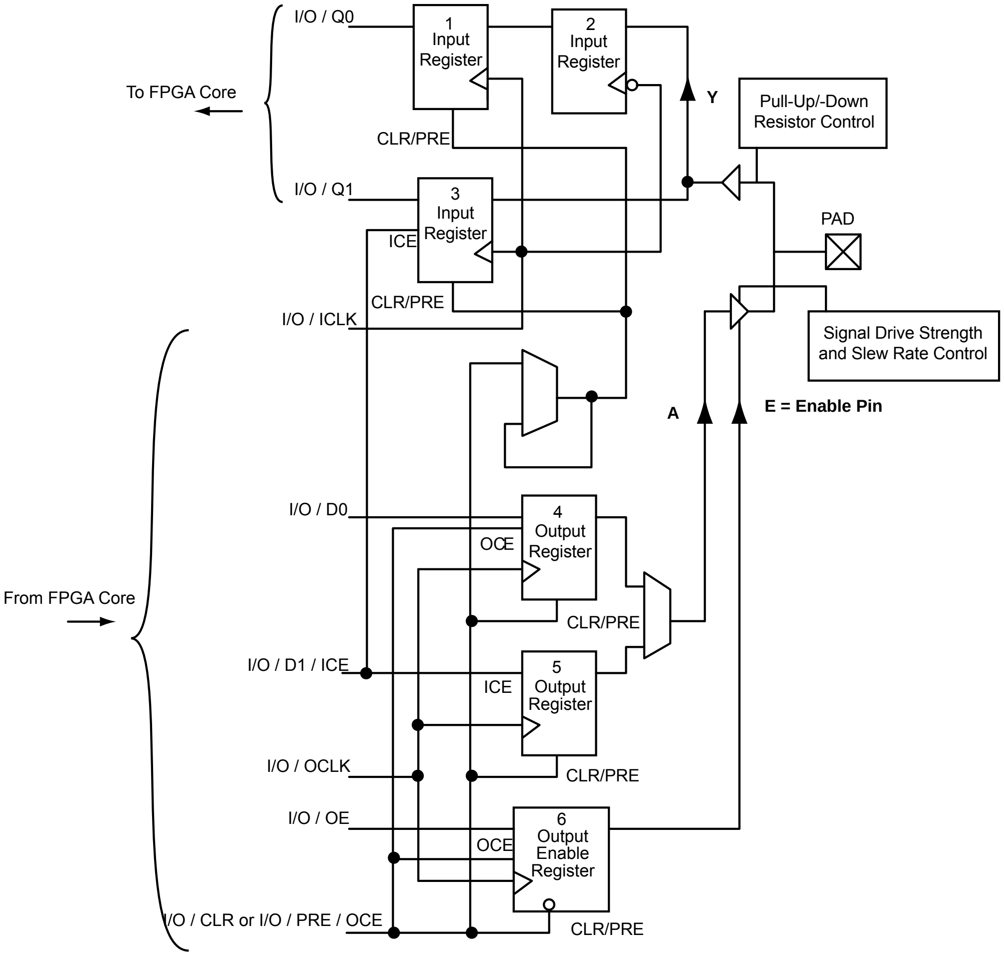


Figure 7-2 • **DDR Configured I/O Block Logical Representation**

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section on page 261).

This feature is supported by all I/O standards.

Rules for Registered I/O Function

1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
    - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.
    - If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
    - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
    - If the clear or preset pins are present, they must have the same polarity.
    - If the clear or preset pins are present, they must be driven by the same signal (net).
3. Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
    - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
    - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a bibuf while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes ------register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

IGLOO and ProASIC3 devices support optional weak pull-up and pull-down resistors on each I/O pin. When the I/O is pulled up, it is connected to the VCCI of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to the "Flash*Freeze Technology and Low Power Modes in IGLOO and ProASIC3L Devices" chapter of the *IGLOO FPGA Fabric User's Guide* or *ProASIC3L FPGA Fabric User's Guide* for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic Low to logic High or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions. Slew rate control is available for LVTTL, LVCMOS, and PCI-X I/O standards. The other I/O standards have a preset slew value.

The slew rate can be implemented by using a PDC command (Table 7-5 on page 179), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 40685).	213, 220
	AGLE1500 was removed from Table 8-2 • Supported I/O Standards because it is not a valid offering. LVCMOS 1.2 was added to the single-ended standards. LVCMOS 1.2 was added to Table 8-3 • VCCI Voltages and Compatible IGLOOe and ProASIC3E Standards (SAR 33207).	215, 217
	Lack of a heading for the "User I/O Naming Convention" section made the information difficult to locate. A heading now introduces the user I/O naming conventions (SAR 38059).	245
	Figure 8-5 • Simplified I/O Buffer Circuitry and Table 8-8 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices (SAR 39666).	222, 227
	The hyperlink for the *Board-Level Considerations* application note was corrected (SAR 36663).	246, 248
June 2011	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	213, 220
	The "Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	215
	Table 8-5 • Legal IGLOOe and ProASIC3E I/O Usage Matrix within the Same Bank was revised as follows (SAR 22467): The combination of 3.3 V I/O bank voltage with 1.50 V minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made an illegal combination (now gray instead of white). The combination of 2.5 V I/O bank voltage with no minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made a valid combination (now white instead of gray).	217
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V–tolerant CMOS input buffer and a push-pull output buffer."	223
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the *Reliability Report* for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	231
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	247
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	214

Table 10-2 • **DDR I/O Options (continued)**

DDR Register Type	I/O Type	I/O Standard	Sub-Options	Comments
Transmit Register (continued)	Tristate Buffer	Normal	Enable Polarity	Low/high (low default)
		LVTTL	Output Drive	2, 4, 6, 8, 12,16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
			Enable Polarity	Low/high (low default)
			Pull-Up/-Down	None (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
			Enable Polarity	Low/high (low default)
			Pull-Up/-Down	None (default)
		PCI/PCI-X	Enable Polarity	Low/high (low default)
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
			Enable Polarity	Low/high (low default)
		HSTL	Class	I / II (I default)
			Enable Polarity	Low/high (low default)
		SSTL2/SSTL3	Class	I / II (I default)
			Enable Polarity	Low/high (low default)
	Bidirectional Buffer	Normal	Enable Polarity	Low/high (low default)
		LVTTL	Output Drive	2, 4, 6, 8, 12, 16, 24, 36 mA (8 mA default)
			Slew Rate	Low/high (high default)
			Enable Polarity	Low/high (low default)
			Pull-Up/-Down	None (default)
		LVCMOS	Voltage	1.5 V, 1.8 V, 2.5 V, 5 V (1.5 V default)
			Enable Polarity	Low/high (low default)
			Pull-Up	None (default)
		PCI/PCI-X	None	
			Enable Polarity	Low/high (low default)
		GTL/GTL+	Voltage	1.8 V, 2.5 V, 3.3 V (3.3 V default)
			Enable Polarity	Low/high (low default)
		HSTL	Class	I / II (I default)
			Enable Polarity	Low/high (low default)
		SSTL2/SSTL3	Class	I / II (I default)
			Enable Polarity	Low/high (low default)

*Note: *IGLOO nano and ProASIC3 nano devices do not support differential inputs.*

Date	Changes	Page
v1.3 (December 2008)	The "Programming Support in Flash Devices" section was updated to include IGLOO nano and ProASIC3 nano devices.	288
	The "Flash Devices" section was updated to include information for IGLOO nano devices. The following sentence was added: IGLOO PLUS devices can also be operated at any voltage between 1.2 V and 1.5 V; the Designer software allows 50 mV increments in the voltage.	289
	Table 11-4 · Programming Ordering Codes was updated to replace FP3-26PIN-ADAPTER with FP3-10PIN-ADAPTER-KIT.	294
	Table 14-6 · Programmer Device Support was updated to add IGLOO nano and ProASIC3 nano devices. AGL400 was added to the IGLOO portion of the table.	317
v1.2 (October 2008)	The "Programming Support in Flash Devices" section was revised to include new families and make the information more concise.	288
	Figure 11-1 · FlashPro Programming Setup and the "Programming Support in Flash Devices" section are new.	287, 288
	Table 14-6 · Programmer Device Support was updated to include A3PE600L with the other ProASIC3L devices, and the RT ProASIC3 family was added.	317
v1.1 (March 2008)	The "Flash Devices" section was updated to include the IGLOO PLUS family. The text, "Voltage switching is required in-system to switch from a 1.2 V core to 1.5 V core for programming," was revised to state, "Although the device can operate at 1.2 V core voltage, the device can only be reprogrammed when the core voltage is 1.5 V. Voltage switching is required in-system to switch from a 1.2 V supply (V_{CC}, V_{CCI}, and V_{JTAG}) to 1.5 V for programming."	289
	The ProASIC3L family was added to Table 14-6 · Programmer Device Support as a separate set of rows rather than combined with ProASIC3 and ProASIC3E devices. The IGLOO PLUS family was included, and AGL015 and A3P015 were added.	317

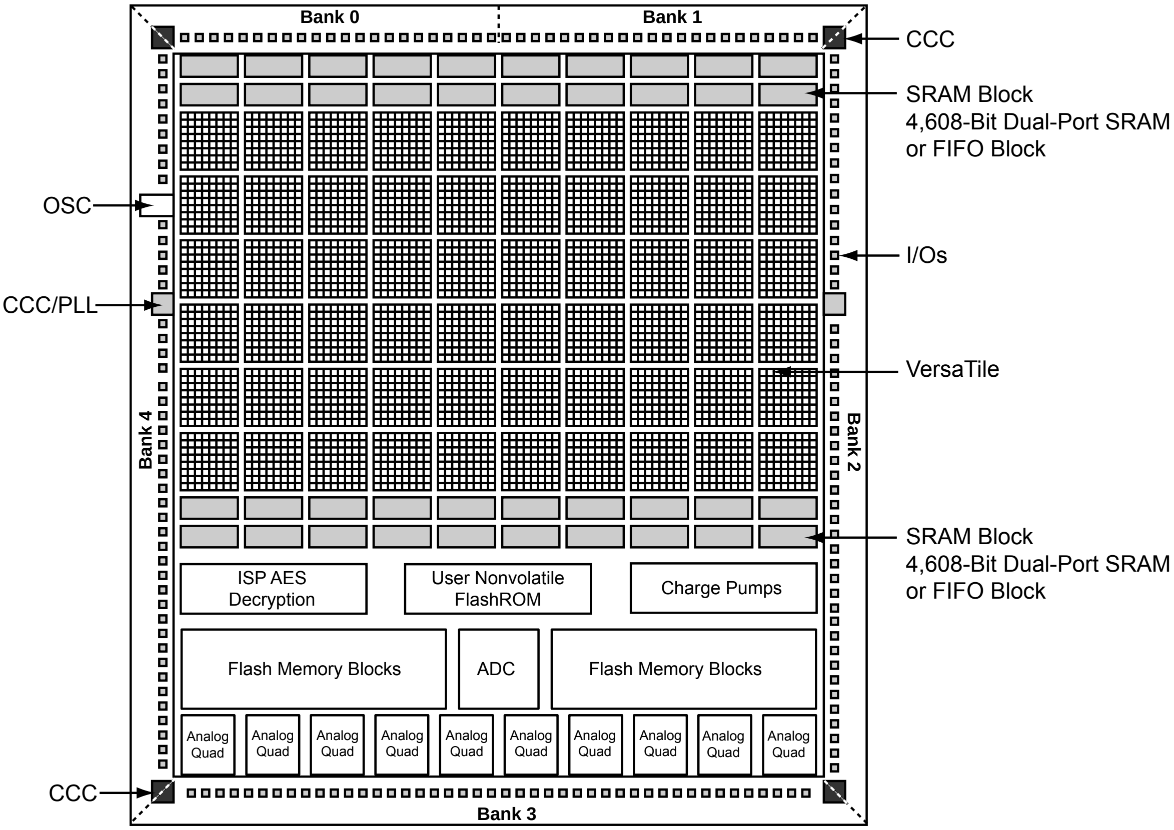


Figure 12-3 • **Block Representation of the AES Decryption Core in a Fusion AFS600 FPGA**

Security Features

IGLOO and ProASIC3 devices have two entities inside: FlashROM and the FPGA core fabric. Fusion devices contain three entities: FlashROM, FBs, and the FPGA core fabric. The parts can be programmed or updated independently with a STAPL programming file. The programming files can be AES-encrypted or plaintext. This allows maximum flexibility in providing security to the entire device. Refer to the "Programming Flash Devices" section on page 287 for information on the FlashROM structure.

Unlike SRAM-based FPGA devices, which require a separate boot PROM to store programming data, low power flash devices are nonvolatile, and the secured configuration data is stored in on-chip flash cells that are part of the FPGA fabric. Once programmed, this data is an inherent part of the FPGA array and does not need to be loaded at system power-up. SRAM-based FPGAs load the configuration bitstream upon power-up; therefore, the configuration is exposed and can be read easily.

The built-in FPGA core, FBs, and FlashROM support programming files encrypted with the 128-bit AES (FIPS-192) block ciphers. The AES key is stored in dedicated, on-chip flash memory and can be programmed before the device is shipped to other parties (allowing secure remote field updates).

Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash devices and the ARM®-enabled flash devices, which have the M1 and M7 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design is encrypted along with the ARM IP, according to the details below.

errors, but this list is intended to show where problems can occur. FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems that may occur with impedance mismatching at higher frequencies. Customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots.

Scan Chain Failure

Normally, the FlashPro4/3/3X Scan Chain command expects to see 0x1 on the TDO pin. If the command reports reading 0x0 or 0x3, it is seeing the TDO pin stuck at 0 or 1. The only time the TDO pin comes out of tristate is when the JTAG TAP state machine is in the Shift-IR or Shift-DR state. If noise or reflections on the TCK or TMS lines have disrupted the correct state transitions, the device's TAP state controller might not be in one of these two states when the programmer tries to read the device. When this happens, the output is floating when it is read and does not match the expected data value. This can also be caused by a broken TDO net. Only a small amount of data is read from the device during the Scan Chain command, so marginal problems may not always show up during this command. Occasionally a faulty programmer can cause intermittent scan chain failures.

Exit 11

This error occurs during the verify stage of programming a device. After programming the design into the device, the device is verified to ensure it is programmed correctly. The verification is done by shifting the programming data into the device. An internal comparison is performed within the device to verify that all switches are programmed correctly. Noise induced by poor signal integrity can disrupt the writes and reads or the verification process and produce a verification error. While technically a verification error, the root cause is often related to signal integrity.

Refer to the *FlashPro User's Guide* for other error messages and solutions. For the most up-to-date known issues and solutions, refer to http://www.microsemi.com/soc/support.

Conclusion

IGLOO, ProASIC3, SmartFusion, and Fusion devices offer a low-cost, single-chip solution that is live at power-up through nonvolatile flash technology. The FlashLock Pass Key and 128-bit AES Key security features enable secure ISP in an untrusted environment. On-chip FlashROM enables a host of new applications, including device serialization, subscription-based applications, and IP addressing. Additionally, as the FlashROM is nonvolatile, all of these services can be provided without battery backup.

Related Documents

User's Guides

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro_ug.pdf

Programming Algorithm

JTAG Interface

The low power flash families are fully compliant with the IEEE 1149.1 (JTAG) standard. They support all the mandatory boundary scan instructions (EXTEST, SAMPLE/PRELOAD, and BYPASS) as well as six optional public instructions (USERCODE, IDCODE, HIGHZ, and CLAMP).

IEEE 1532

The low power flash families are also fully compliant with the IEEE 1532 programming standard. The IEEE 1532 standard adds programming instructions and associated data registers to devices that comply with the IEEE 1149.1 standard (JTAG). These instructions and registers extend the capabilities of the IEEE 1149.1 standard such that the Test Access Port (TAP) can be used for configuration activities. The IEEE 1532 standard greatly simplifies the programming algorithm, reducing the amount of time needed to implement microprocessor ISP.

Implementation Overview

To implement device programming with a microprocessor, the user should first download the C-based STAPL player or DirectC code from the Microsemi SoC Products Group website. Refer to the website for future updates regarding the STAPL player and DirectC code.

http://www.microsemi.com/soc/download/program_debug/stapl/default.aspx

http://www.microsemi.com/soc/download/program_debug/directc/default.aspx

Using the easy-to-follow user's guide, create the low-level application programming interface (API) to provide the necessary basic functions. These API functions act as the interface between the programming software and the actual hardware (Figure 15-2).

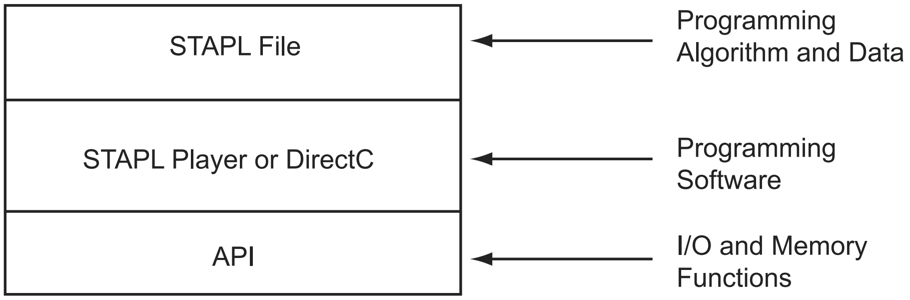


Figure 15-2 • **Device Programming Code Relationship**

The API is then linked with the STAPL player or DirectC and compiled using the microprocessor's compiler. Once the entire code is compiled, the user must download the resulting binary into the MCU system's program memory (such as ROM, EEPROM, or flash). The system is now ready for programming.

To program a design into the FPGA, the user creates a bitstream or STAPL file using the Microsemi Designer software, downloads it into the MCU system's volatile memory, and activates the stored programming binary file (Figure 15-3 on page 352). Once the programming is completed, the bitstream or STAPL file can be removed from the system, as the configuration profile is stored in the flash FPGA fabric and does not need to be reloaded at every system power-on.

Figure 18-3 **• I/O State when VCCI Is Powered before VCC**

Power-Up to Functional Time

At power-up, device I/Os exit the tristate mode and become functional once the last voltage supply in the power-up sequence (VCCI or VCC) reaches its functional activation level. The power-up–to–functional time is the time it takes for the last supply to power up from zero to its functional level. Note that the functional level of the power supply during power-up may vary slightly within the specification at different ramp-rates. Refer to Table 18-2 for the functional level of the voltage supplies at power-up.

Typical I/O behavior during power-up–to–functional time is illustrated in Figure 18-2 on page 377 and Figure 18-3.

Table 18-2 **• Power-Up Functional Activation Levels for VCC and VCCI**

Device	VCC Functional Activation Level (V)	VCCI Functional Activation Level (V)
ProASIC3, ProASIC3 nano, IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.5 V*	0.85 V ± 0.25 V	0.9 V ± 0.3 V
IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices running at VCC = 1.2 V*	0.85 V ± 0.2 V	0.9 V ± 0.15 V

Note: **V5 devices will require a 1.5 V* VCC *supply, whereas V2 devices can utilize either a 1.2 V or 1.5 V* VCC.

Microsemi's low power flash devices meet Level 0 LAPU; that is, they can be functional prior to V_{CC} reaching the regulated voltage required. This important advantage distinguishes low power flash devices from their SRAM-based counterparts. SRAM-based FPGAs, due to their volatile technology, require hundreds of milliseconds after power-up to configure the design bitstream before they become functional. Refer to Figure 18-4 on page 379 and Figure 18-5 on page 380 for more information.

A – Summary of Changes

History of Revision to Chapters

The following table lists chapters that were affected in each revision of this document. Each chapter includes its own change history because it may appear in other device family user's guides. Refer to the individual chapter for a list of specific changes.

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 4 (September 2012)	"Microprocessor Programming of Microsemi's Low Power Flash Devices" was revised.	356
Revision 3 (August 2012)	"FPGA Array Architecture in Low Power Flash Devices" was revised.	20
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"SRAM and FIFO Memories in Microsemi's Low Power Flash Devices" was revised.	173
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	The "Pin Descriptions" and "Packaging" chapters were removed. This information is now published in the datasheet for each product line (SAR 34773).	
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Boundary Scan in Low Power Flash Devices" was revised.	362
Revision 2 (December 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"UJTAG Applications in Microsemi's Low Power Flash Devices" was revised.	372
Revision 1 (June 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	"I/O Software Control in Low Power Flash Devices" was revised.	270
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
Revision 0 (July 2010)	The ProASIC3L Flash Family FPGAs Handbook was divided into two parts to create the ProASIC3L Low Power Flash FPGAs Datasheet and the ProASIC3L FPGA Fabric User's Guide.	N/A
	"Global Resources in Low Power Flash Devices" was revised.	75
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Software Control in Low Power Flash Devices" was revised.	270